


REMARKS:

This is a preliminary amendment of the above-referenced application. Applicant cancels claim 1 of the present application and adds new claims 13-15 to the present application. Applicant further amends claim 10 of the present application; marked up version of the amended claim is attached hereto pursuant to 37 C.F.R. § 1.121(c)(ii). Pursuant to this amendment, claims 10-15 are pending. Applicant respectfully submits that all pending claims distinguish over the art of record and are in condition for allowance.

If for any reason the Examiner finds the application other than in condition for allowance, the Examiner is requested to call the undersigned attorney at the Los Angeles, California telephone number (213) 337-6870 to discuss the steps necessary for placing the application in condition for allowance.

If there are any fees due in connection with the filing of this response, please charge the fees to our Deposit Account No. 50-1314.

Respectfully submitted,
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Version with markings to show changes made:

10. (Amended) A semiconductor device having a plurality of semiconductor elements on a substrate, wherein some or all of the semiconductor elements [have] each has a plurality of channel areas (a) which are formed in a semiconductor layer subjected to laser annealing respectively, and (b) which are the same conductive type channel areas, and the plurality of channel areas are electrically connected [in parallel] to each other and arranged separately [and/or arranged] and in different directions to each other.

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